

ABSTRACT OF THE DISCLOSURE

Light-emitting diode chip having a semiconductor layer sequence with an active zone that emits electromagnetic radiation and an electrical contact structure comprising a radiation-transmissive electrical current expansion layer, which contains ZnO, and an electrical connection layer. The current expansion layer comprises a window, in which the connection layer is applied on a cladding layer of the semiconductor layer sequence, the connection layer being electrically conductively connected to the current expansion layer. In addition, the junction between the connection layer and the cladding layer, in the event of an electrical voltage being applied to the light-emitting diode chip in the operating direction, is not electrically conductive or is only so poorly electrically conductive that the entire, or virtually the entire, current flows via the current expansion layer.